

Vishay Semiconductors

Insulated Ultrafast Rectifier Module, 200 A



SOT-227

PRODUCT SUMMARY					
t _{rr}	102 ns				
$I_{F(AV)}$ at $T_C = 105 ^{\circ}C$	200 A				
V_{R}	600 V				

FEATURES

- Two fully independent diodes
- Ceramic fully insulated package (V_{ISOL} = 2500 V_{AC})
- Ultrafast reverse recovery
- Ultrasoft reverse recovery current shape
- Low forward voltage
- Optimized for power conversion: Welding and industrial SMPS applications
- Industry standard outline
- Plug-in compatible with other SOT-227 packages
- · Easy to assemble
- · Direct mounting to heatsink
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC

DESCRIPTION

The UFL200FA60P insulated modules integrate two state of the art Vishay Semiconductors ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The planar structure of the diodes, and the platinum doping life-time control, provide a ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V_{R}		600	V	
Continuous forward current per diode	I _F	T _C = 85 °C	144	Α	
Single pulse forward current per diode	I _{FSM}	T _C = 25 °C	1000		
Maximum power dissipation per module	P _D	T _C = 85 °C	360	W	
Isolation voltage	V _{ISOL}	Any terminal to case, t = 1 min	2500	V	
Operating junction and storage temperatures	T _J , T _{Stg}		- 55 to 175	°C	

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA	600	-	-	
Forward voltage V _{FM}		I _F = 100 A	-	1.28	1.44	
	V_{FM}	I _F = 200 A	-	1.48	1.66	V
		I _F = 100 A, T _J = 125 °C	-	1.13	1.24	
		I _F = 200 A	-	1.37	1.55	
Reverse leakage current I _{RM}		$V_R = V_R$ rated	-	5	100	μA
	IRM	T _J = 175 °C, V _R = V _R rated	-	0.2	1	mA
Junction capacitance	C _T	V _R = 600 V	-	80	-	pF

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Davis and the same of the same	+	T _J = 25 °C	- I _F = 50 A	102	141		
Reverse recovery time	t _{rr}	T _J = 125 °C		-	210	293	ns
Post and a second	1	T _J = 25 °C		-	9	12	А
Peak recovery current	ak recovery current I _{RRM}	T _J = 125 °C		-	21	25	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	443	744	nC
	Q _{rr}	T _J = 125 °C		-	2086	3355	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	Б		-	-	0.5	°C/W
Junction to case, both leg conducting	R _{thJC}		-	-	0.25	K/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	1.3	-	Nm



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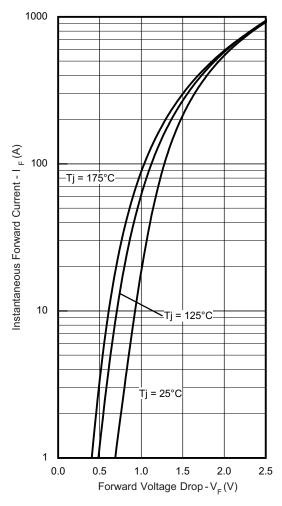


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Diode)

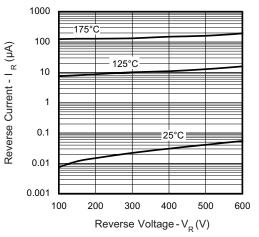


Fig. 1 - Typical Values of Reverse Current vs. Reverse Voltage

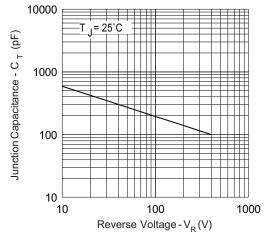


Fig. 2 - Typical Junction Capacitance vs. Reverse Voltage

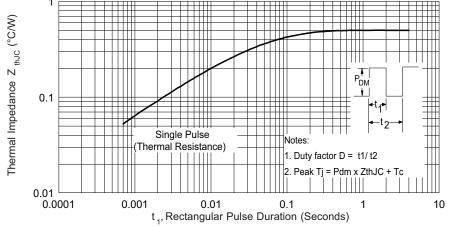


Fig. 3 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Diode)

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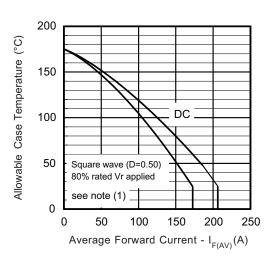


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

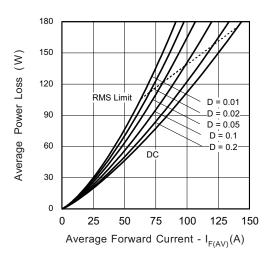


Fig. 5 - Forward Power Loss Characteristics (Per Leg)

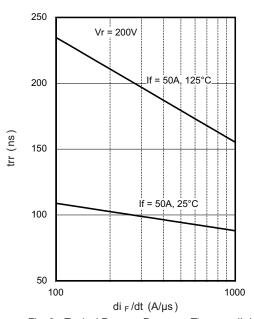


Fig. 6 - Typical Reverse Recovery Time vs. dI_{F}/dt

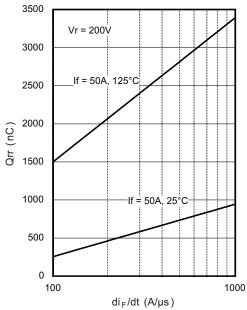


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = 80 % rated V_R





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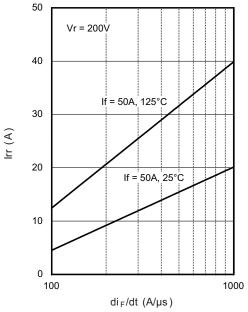


Fig. 9 - Typical Stored Current vs. dl_F/dt

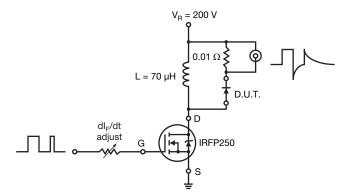
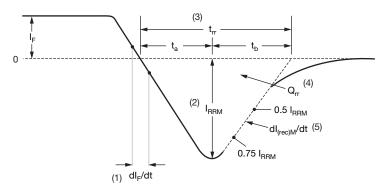


Fig. 10 - Reverse Recovery Parameter Test Circuit

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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

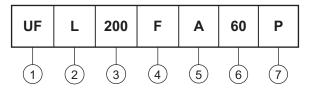
$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

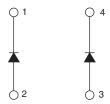
ORDERING INFORMATION TABLE

Device code



- Ultrafast rectifier
- 2 Ultrafast Pt low V_F
- 3 Current rating (200 = 200 A)
- Circuit configuration (2 separate diodes, parallel pin-out)
- 5 Package indicator (SOT-227 standard isolated base)
- 6 Voltage rating (60 = 600 V)
- 7 P = Lead (Pb)-free

CIRCUIT CONFIGURATION



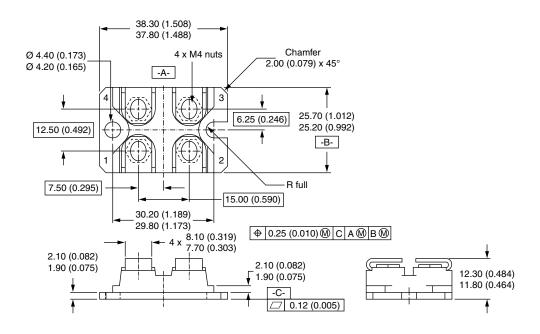
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95036					
Packaging information	www.vishay.com/doc?95037				



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DIMENSIONS in millimeters (inches)



Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter

Document Number: 95036 Revision: 28-Aug-07



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